

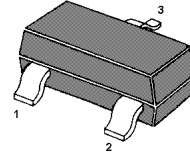
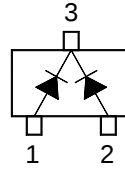
1SS392

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low voltage high speed switching application

Features

- Low forward voltage
- Low reverse current



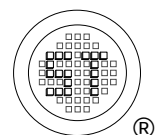
Marking Code: "ZD"
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current ($t = 10$ ms)	I_{FSM}	1	A
Power Dissipation	P_d	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 100$ mA	V_F	-	0.6	V
Reverse Current at $V_R = 40$ V	I_R	-	5	μA
Reverse Breakdown Voltage at $I_R = 10$ μA	$V_{(BR)R}$	45	-	V
Total Capacitance at $V_R = 0$, $f = 1$ MHz	C_T	-	25	pF



Dated : 04/12/2007

